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# Wide Bandgap Semiconductor Materials and Devices 12

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## Table of Contents

*Preface* *iii*

### Chapter 1 Wide Bandgap Nanostructures

(Invited) III-Nitride Nanowires: Emerging Materials for Lighting and Energy Applications 3

*G. T. Wang, Q. Li, J. Huang, J. Wierer, A. Armstrong, Y. Lin, P. Upadhyya, and R. Prasankumar*

Ultra-Thin GaN Membranes Fabricated by Using Surface Charge Lithography 13

*I. Tiginyanu, V. Popa, and M. A. Stevens-Kalceff*

Electrical and Proton Conduction Properties of Amorphous TiO<sub>2</sub> Nanotubes Fabricated by Electrochemical Anodization 21

*I. Hanzu, T. Djenizian, and P. Knauth*

### Chapter 2 Wide Bandgap LEDs and Solar Cells

(Invited) High Thermal Dissipation Apparatus for UV LEDs Application 35

*R. Horng, H. Hu, R. Lin, and Y. Chiang*

Molecular Beam Epitaxial Growth, Fabrication, and Characterization of High Efficiency InGaN/GaN Dot-in-a-Wire White Light Emitting Diodes on Si(111) 41

*H. P. Nguyen, S. Zhang, K. Cui, X. Han, and Z. Mi*

Growth and Characterization of p-InGaN/i-InGaN/n-GaN Double Heterojunction Solar Cell on Patterned Sapphire Substrates 47

*M. Chu, W. Liao, M. Wu, R. Horng, T. Tsai, and S. Liu*

A Novel InGaN Blue Light-Emitting Diode with a Self-Textured Oxide Mask Structure 53

*W. Lin, D. Wu, S. Huang, S. Lo, C. Liu, and R. Horng*

### Chapter 3 Growth of Wide Bandgap Materials

(Invited) Experimental Evidence that the Plasma-Assisted MBE Growth of Nitride Alloys is a Liquid Phase Epitaxy Process <i>T. D. Moustakas and A. Bhattacharyya</i>	63
Effect of Growth Parameters on Stress in HVPE GaN Films <i>A. Tsyuk, R. Gorbunov, V. Voronenkov, Y. Lelikov, P. Latyshev, A. Zubrilov, Y. Rebane, N. Bochkareva, and Y. Shreter</i>	73
Microstructure Characterization of Cu-Alloyed GaN Grown by Plasma Assisted Molecular Beam Epitaxy <i>T. Huang, P. Ganz, L. Chang, D. Schaadt, and J. Bao</i>	83
Thick GaN Films Grown on Patterned Sapphire Substrates <i>V. Voronenkov, R. Gorbunov, A. Tsyuk, P. Latyshev, Y. Lelikov, Y. Rebane, A. Zubrilov, N. Bochkareva, and Y. Shreter</i>	91
3C-SiC Film Growth on Si Substrates <i>A. Severino, C. Locke, R. Anzalone, M. Camarda, N. Piluso, A. La Magna, S. Sadow, G. Abbondanza, G. D'Arrigo, and F. La Via</i>	99
High Power Density UV Optical Stress for Quality Evaluation of 4H-SiC Epitaxial Layers <i>A. Canino, M. Camarda, and F. La Via</i>	117
Advanced Residual Stress Analysis on the Heteroepitaxial Growth of 3C-SiC/Si for MEMS Application <i>R. Anzalone, M. Camarda, G. D'Arrigo, N. Piluso, A. Severino, A. Canino, A. La Magna, and F. La Via</i>	123
Growth Behavior of M-Plane ZnO Epilayer on (100) LiGaO <sub>2</sub> by Chemical Vapor Deposition <i>J. Yu, T. Huang, L. Chang, M. Chou, and D. Gan</i>	133
Influence of Doping and Co-Doping on the Behavior of Sputtered ZnO Thin Films <i>K. S. Shtereva, P. Sutta, B. Pecz, I. Novotny, J. Kovac, and V. Tvarozek</i>	141
Role of Zn-Interstitial Defect in the Ultraviolet Emission from ZnO <i>M. Hashmi, K. Mahmood, A. Ali, M. Hasan, M. Raja, I. Hussain, and M. Willander</i>	149

## Chapter 4 Wide Bandgap Electronic Devices

Nitrided Gate Oxide Formed by Rapid Thermal Processing for 4H-SiC MOSFETs <i>A. Constant, P. Godignon, J. Montserrat, and J. Millán</i>	157
Two-State Current Conduction in High-k/SiO <sub>2</sub> Stacked Dielectric with High Bandgap 4H-SiC Substrate <i>J. Chiang and J. Hwu</i>	165
Characteristics of 4H-SiC RF MOSFETs on a Semi-Insulating Substrate <i>T. Wu, C. Huang, and C. Cheng</i>	173
Effects of SiO <sub>2</sub> Passivation on Oxygen Annealed AlGaN/GaN HEMTs <i>O. Seok, Y. Kim, M. Ha, and M. Han</i>	185
Vertically Configured Nanodiamond Vacuum Field Emission Transistor Arrays <i>S. Hsu, W. P. Kang, J. Davidson, and J. Huang</i>	191
The Effect of Different Carrier Gases and Channel Thicknesses on the Characteristics of ZnO TFTs Prepared by Atmospheric Pressure Plasma Jet <i>K. Chang, S. Huang, C. Chi, C. Wu, J. Lin, and C. Chang</i>	199
Author Index	209